



HyperRAM™

DRAM Based Memory with HyperBus™ Interface

► Features:

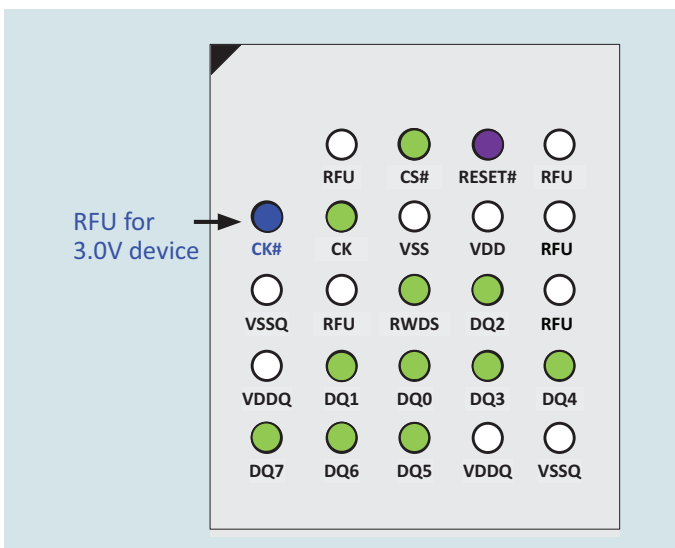
- Hidden Refresh operation
- Very Low Bus Signal Count :
 - 12 pins for 1.8V [with CK,CK#]
 - 11 pins for 3.0V [CK only]
- Max. Frequency :
 - 166MHz at VDD = 1.8V
 - 100MHz at VDD = 3.0V
- Low Power Consumption :
 - Burst Operation Current at 166MHz, 1.8V = 60mA [Max]
 - Standby Current @ 105°C, 1.8V = 300uA [Max]
 - Deep Power Down Current @ 105°C, 1.8V = 10uA [Max]

► Package:

- KGD/KTD
- 24-pin BGA

► HyperRAM™ Pin-Outs (In evaluation):

- 24-pin [5 x 5 ball array]
- PKG Body Size : 6 mm x 8 mm
- Ball Pitch : 1.0mm



► Densities:

- 64Mb [8Mb x 8] , 32Mb [4Mb x8],
- 128Mb [16Mb x8], 256Mb [32Mb x8]

► Availability:

- 64Mb
 - Production Now!
- 128Mb
 - Samples Available Now!
- 32Mb, 256Mb
 - Call Factory

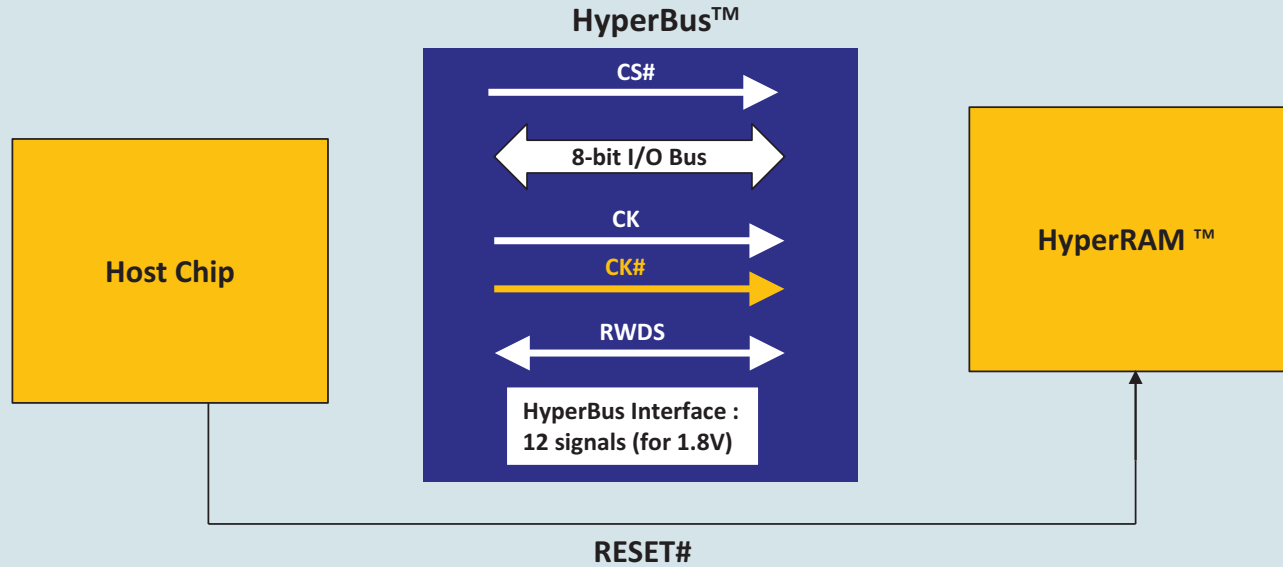
► Automotive Temperature Grades:

- Automotive, A1 [-40°C to 85°C]
- Automotive, A2 [-40°C to 105°C]

► Applications:

- Infotainment
- Advanced Driver Assistance Systems
- Smart Appliance
- Factory Automation
- Medical
- LED Projector
- D-SLR Camera
- Auto-Cluster

HyperRAM™ Interface



► Low Signal Pin Count for HyperBus™:

- 12 signals for 1.8V Device [with CK,CK#]
- 11 signals for 3.0V Device [with CK only]
- * RESET# is not included in the HyperBus™ signal.
- Differential Clock [CK,CK#] for 1.8V device & Single Ended Clock [CK only] for 3.0V device
- Up to 166MHz Double-Data-Rate [DDR] 8-bit I/O bus for high throughput : 333 MB/s bandwidth
- Read Write Data Strobe [RWDS] to:
 - Indicate Refresh Collision
 - Edge Aligned with Read Data for Read Operations
 - Byte mask for write operations
- Clocks [CK,CK#] are not required to be free-running